

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLN. OF: ASPAR et al.

FILED: February 23, 2004

FOR: A METHOD OF PRODUCING A THIN LAYER OF ...

DOCKET: BREV 12370 CON4

MAIL STOP PATENT APPLICATION

Commissioner for Patents

P.O. Box 1450

Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Dear Sir:

In connection with the above-entitled matter, Applicants hereby proffer U.S. Patent Office Forms PTO-1449 and PTO-892. The present application is a continuation under 37 CFR 1.53(b) of application Serial No. 09/777,516, wherein the references referred to in the enclosed U.S. Patent Office Forms PTO-1449 and PTO-892 have been previously submitted or cited. Accordingly, it is respectfully submitted that no copies of these references are believed necessary. The claims in the present application are believed to be patentably distinguished over these references.

This information disclosure statement is being made pursuant to the duty of disclosure imposed by law and formulated in 37 CFR 1.56(A). No representation is made that the information thus disclosed in fact constitutes prior art or that it is the closest prior art, inasmuch as 37 CFR 1.56(A) relies on a materiality concept which depends on subjectivity.

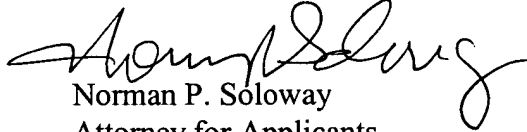
HAYES SOLOWAY P.C.

130 W. CUSHING ST.
TUCSON, AZ 85701
TEL. 520.882.7623
FAX. 520.882.7643

175 CANAL STREET
MANCHESTER, NH 03101
TEL. 603.668.1400
FAX. 603.668.8567

In the event there are any fee deficiencies or additional fees are payable, please charge them (or credit any overpayment) to our Deposit Account No. 08-1391.

Respectfully submitted,




Norman P. Soloway
Attorney for Applicants
Reg. No. 24,315

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I hereby certify that this paper and the papers listed thereon are being deposited with the United States Postal Service "Express Mail Post Office to Addressee" service under 37 CFR 1.10 on the date indicated above, and is addressed to MAIL STOP PATENT APPLICATION, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

Signature of person mailing: 

Name of person mailing: Shauna Bronson

NPS:sb

HAYES SOLOWAY P.C.

130 W. CUSHING ST.
TUCSON, AZ 85701
TEL. 520.882.7623
FAX. 520.882.7643

175 CANAL STREET
MANCHESTER, NH 03101
TEL. 603.668.1400
FAX. 603.668.8567

INFORMATION DISCLOSURE CITATION
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Docket Number (Optional)

BREV 12370 C

Application Number

Applicant(s)

ASPAR ET AL

Filing Date

Group A

COPY

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
Dac		5,256,581	10/26/93	FOERSTNER ET AL	437	24	
Dal		6,020,252	2/1/00	ASPAR ET AL	438	458	

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09/777516
02/06/01

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	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER

D.B. Courts

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12-21-01

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INFORMATION DISCLOSURE CITATION
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ATTY DOCKET NO.
BREV 12370 CON 2

SERIAL NO.

ASPAR ET AL

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U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
Dac	4,704,302	11/3/87	Bruel et al			
	5,234,535	8/10/93	NBeyer et al			
	5,494,835	2/27/96	Bruel			
	5,804,086	9/8/98	Bruel			
	5,817,368	10/6/98	Hashimoto			
	5,863,830	1/26/99	Bruel et al			
	5,897,331	4/27/99	Sopori			
	5,633,174	5/27/97	Li			
	5,250,446	10/5/93	Osowa et al			

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						YES	NO
Dac	WO95/20824	8/3/95	PCT			✓	
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	0 660 140	6/28/95	EPO			✓	
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D.M. Cousins

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FORM PTO-1449	SERIAL NO.	CASE NO. BREV 12370 CON 2
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	FILING DATE	GROUP ART UNIT
(use several sheets if necessary)	APPLICANT(S): Aspar et al.	

REFERENCE DESIGNATION

U.S. PATENT DOCUMENTS

U.S. PATENTS

<u>PATENT NO.</u>	<u>INVENTOR</u>	<u>ISSUE DATE</u>
4,179,324	12/18/79	Kirkpatrick
5,110,748	5/5/92	Sarma
5,310,446	5/10/94	Konishi et al.
5,661,333	8/26/97	Bruel et al.

FOREIGN PATENTS

<u>DOCUMENT NO.</u>	<u>COUNTRY</u>	<u>DATE</u>
2725074	France	March 29, 1996
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D. A. Collins

12-21-01

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<i>Dme</i>	A1	4,179,324	12/18/79	Kirkpatrick	156/230	11/28/77
	A2	5,110,748	5/5/92	Sarma	437/51	7/22/91
	A3	5,310,446	5/10/94	Konishi et al.	117/58	7/13/92
	A4	5,661,333	8/26/97	Bruel et al.	257/618	1/25/95
	A5					
	A6					
	A7					
	A8					

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EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS/ SUBCLASS	TRANSLATION YES	NO
<i>Dme</i>	A9	2725074	3/29/96	France			X
	A10	0355913	2/28/90	EPO		X	
	A11	0504714	9/23/92	EPO		X	

EXAMINER INITIAL	OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)	
<i>Dme</i>	A12	Silicon-On-Insulator, <i>European Semiconductor</i> , March, 1997, pages 17 and 18
	A13	Aspar et al., SMART-CUT®: The basic fabrication process for UNIBOND® SOI wafers, <i>SEMI</i> 1996, pp. 37-46
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	A15	Hamaguchi et al., Device Layer Transfer Technique using Chemo-Mechanical Polishing, <i>Japanese Journal of Applied Physics</i> , 23(1984), Oct., No. 10, Part 2, Tokyo, Japan, pp. L815-L817
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EXAMINER <i>D.M. Collins</i>	DATE CONSIDERED <i>12-21-01</i>
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Dmc	4,931,405	06/05/1990	KAMIJO ET AL	437	12	
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						YES	NO
Dmc	53-104156	09/11/1978	JAPAN	H01L	21/322		✓
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Dmc		WILLIAM PRIMAK ET AL IMPURITY EFFECT IN THE IONIZATION DILATATION OF VITREOUS SILICA 1967

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Dmc	ERROL P. EERNISSE, COMPACTION OF ION-IMPLANTED FUSED SILICA, 1973
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Applicant(s)
ASPAR ET AL

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PAGE 11 OF 16

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COPY

U.S. PATENT DOCUMENTS

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FOREIGN PATENT DOCUMENTS

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Dme			La Formation Des Cloques, Saint-Jacques, Nuclear Instruments and Methods 209/210 (1983), pgs. 333-343
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Doc		Helium Bubble and Blister Formation for Nickel and An AMorphous Fe-Ni-Mo-B Alloy During 5 keV He+-Irradiation at Temperatures Between 200 K and 600 K, Swijgenhoven, Stals and Knuyt, Nuclear Instruments and Methods 209/210 (1983) pgs. 461-468
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Dmc		Silicon-on-insulator produced by helium implantation and thermal oxidation, Raineri, Campisano, Appl. Phys. Lett. 66 (26), 26 June 1995, pgs. 3654-3656
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PAGE 14 OF 16

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Dme			Ion Implantation In Semiconductors 1976, Chernow, Borders and Brice, Plenum Press, New York and London, Radiation Damage of 50-250 keV Hydrogen Ions in Silicon, Chu, Kastle, Lever, Mader and Masters, S, pgs. 483-491

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FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE
(Modified) PATENT AND TRADEMARK OFFICE

INFORMATION DISCLOSURE
STATEMENT BY APPLICANT

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(37 CFR 1.98(b))

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